Unit: mm

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT40Q323

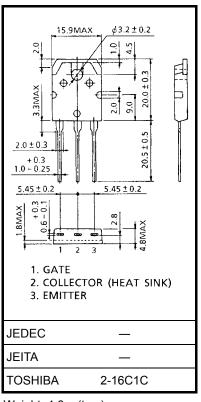
Voltage Resonance Inverter Switching Application

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- Enhancement-mode
- High speed: $t_f = 0.14 \ \mu s$ (typ.) (I_C = 40A)
- FRD included between emitter and collector
- 4th generation
- TO-3P (N) (Toshiba package name)

Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1200	V	
Gate-emitter voltage		V _{GES}	±25	V	
Continuous collector current	@ Tc = 100°C	la	20	A	
	@ Tc = 25°C	IC	39		
Pulsed collector current		I _{CP}	80	А	
Diode forward current	DC	١ _F	10	A	
	Pulsed	I _{FP}	80		
Collector power dissipation	@ Tc = 100°C	De	80	W	
	@ Tc = 25°C	P _C	200		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Weight: 4.6 g (typ.)

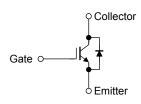
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance (IGBT)	R _{th (j-c)}	0.625	°C/W	
Thermal resistance (diode)	R _{th (j-c)}	1.79	°C/W	

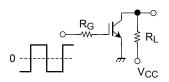
Equivalent Circuit

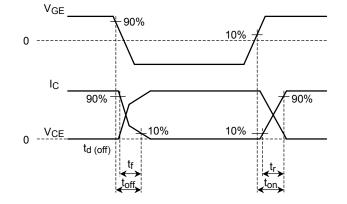


Electrical Characteristics (Ta = 25°C)

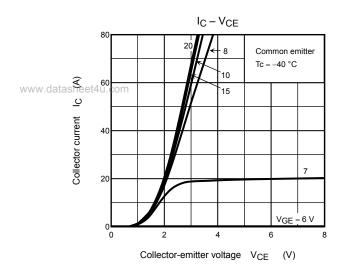
	Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
	Gate leakage current Collector cut-off current		IGES	V_{GE} = ±25 V, V_{CE} = 0	—	_	±500	nA
			ICES	V _{CE} = 1200 V, V _{GE} = 0	_	_	5.0	mA
Co Inp	Gaté-emitter cut-off voltage		V _{GE (OFF)}	$I_{\rm C}$ = 40 mA, $V_{\rm CE}$ = 5 V	4.0	_	7.0	V
	Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 40 A, V _{GE} = 15 V	_	3.0	3.7	V
	Input capacitance		Cies	V_{CE} = 10 V, V_{GE} = 0, f = 1 MHz	—	5550	-	pF
	Switching time Fall	Rise time	t _r	Resistive Load	_	0.18	_	
		Turn-on time	t _{on}	V _{CC} = 600 V, I _C = 40 A	—	0.26	—	μs
		Fall time	t _f	V_{GG} = ±15 V, R _G = 39 Ω	_	0.14	0.21	μο
		Turn-off time	t _{off}	(Note 1)	_	0.43	_	
	Diode forward voltage Reverse recovery time		VF	I _F = 10 A, V _{GE} = 0	_	_	2.1	V
			t _{rr}	I _F = 10 A, di/dt = −20 A/µs	_	0.4	_	μs

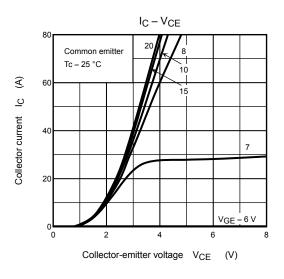
Note 1: Switching time measurement circuit and input/output waveforms

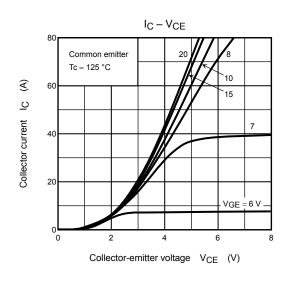


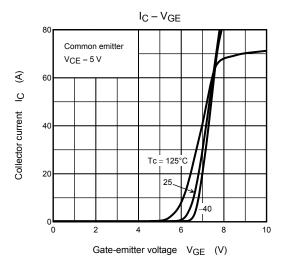


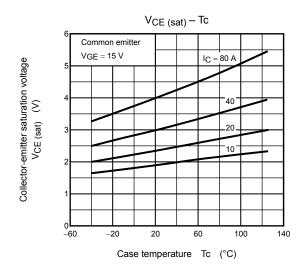
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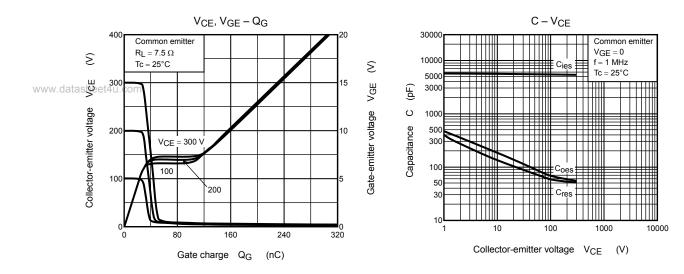


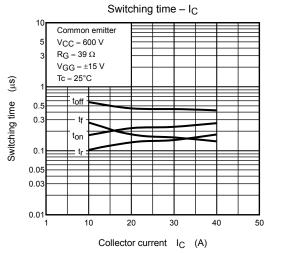




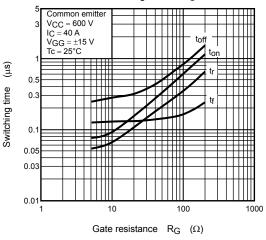


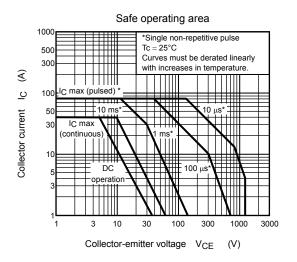
TOSHIBA

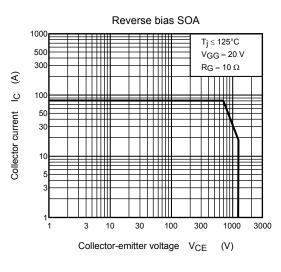




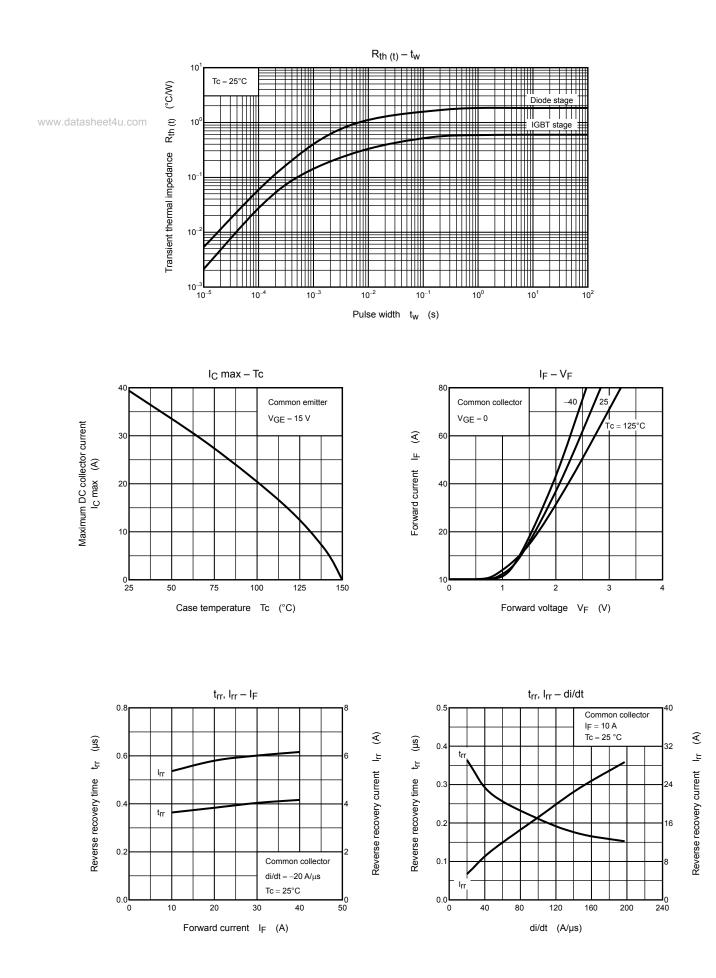
Switching time – R_G







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